

L Number	Hits	Search Text	DB	Time stamp
1	0	"6649287"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 15:55
2	2	"20020074552"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 16:06
3	14	"763972"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 15:56
4	0	20020074552.URPN.	USPAT	2003/11/05 16:06
5	0	20020074552.URPN.	USPAT	2003/11/05 16:06
6	409	257/190.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 16:07
7	199	257/190.ccls. and (Gallium or AlGaN or GaN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 16:13
8	0	((Gallium near3 nitride\$1) or AlGaN or GaN) with epitaxil	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 16:15
9	0	((Gallium near3 nitride\$1) or AlGaN or GaN) with epitax*5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 16:16
10	1901	((Gallium near3 nitride\$1) or AlGaN or GaN) with epitax\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 16:16
11	27	((Gallium near3 nitride\$1) or AlGaN or GaN) with epitax\$5) and ((Gallium near3 nitride\$1) or AlGaN or GaN) with ((silicon near germanium) or SiGe or "Si.sub.x Ge.sub.1-x")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 16:48
12	14	((Gallium near3 nitride\$1) or AlGaN or GaN) and (((silicon near germanium) or SiGe or "Si.sub.x Ge.sub.1-x") with graded)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 18:10
13	368	((Gallium near3 nitride\$1) or AlGaN or GaN) same (((silicon near germanium) or SiGe or "Si.sub.x Ge.sub.1-x"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 17:05
14	19	((Gallium near3 nitride\$1) or AlGaN or GaN) and (((silicon near germanium) or SiGe or "Si.sub.x Ge.sub.1-x") with buffer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 17:41
15	0	19802977.URPN.	USPAT	2003/11/05 17:17

16	2608	((Gallium near3 nitride\$1) or AlGaN or GaN) and (((silicon near germanium) or SiGe or "Si.sub.x Ge.sub.1-x" or silicon or GeSi or Si) near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 17:23
17	2367	((Gallium near3 nitride\$1) or AlGaN or GaN) and (((silicon near germanium) or SiGe or "Si.sub.x Ge.sub.1-x" or silicon or GeSi or Si) near2 substrate)) and (((silicon near germanium) or SiGe or "Si.sub.x Ge.sub.1-x" or silicon or GeSi))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 17:24
18	574	((Gallium near3 nitride\$1) or AlGaN or GaN) and (((silicon near germanium) or SiGe or "Si.sub.x Ge.sub.1-x" or silicon or GeSi or Si) near2 substrate)) and (((silicon near germanium) or SiGe or "Si.sub.x Ge.sub.1-x" or silicon or GeSi) with buffer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 17:25
19	356	((Gallium near3 nitride\$1) or AlGaN or GaN) and (((silicon near germanium) or SiGe or "Si.sub.x Ge.sub.1-x" or silicon or GeSi or Si) near2 substrate)) and (((silicon near germanium) or SiGe or "Si.sub.x Ge.sub.1-x" or silicon or GeSi) near3 buffer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 17:27
20	22	((Gallium near3 nitride\$1) or AlGaN or GaN) and (((silicon near germanium) or SiGe or "Si.sub.x Ge.sub.1-x" or silicon or GeSi or Si) near2 substrate)) and (((silicon near germanium) or SiGe or "Si.sub.x Ge.sub.1-x" or GeSi) near3 buffer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 17:27
21	2	"6464780" and GaN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 17:42
26	2	"20030011000"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 17:50
33	6	((Gallium near3 nitride\$1) or AlGaN or GaN) with (((silicon near germanium) or SiGe or "Si.sub.x Ge.sub.1-x") near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/05 18:10